

AMENDMENTS TO THE SPECIFICATION:

Please cancel the Abstract (page 22) and replace it with the following Abstract:

A method including a buried layer formed on a semiconductor substrate, an active region formed adjacent to at least a portion of the buried layer, an isolation structure formed adjacent to at least a portion of the active region, and a gate oxide formed adjacent to at least a portion of the active region. The method also includes a polysilicon layer formed adjacent to at least a portion of the gate oxide having a portion removed to form a polysilicon definition structure that substantially surrounds and defines an emitter contact region. The method also includes forming a self-aligned implant region of the emitter contact region.